

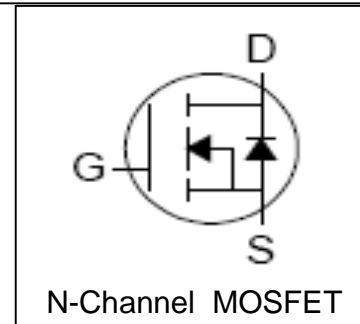
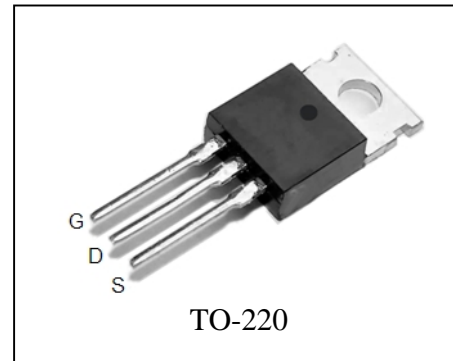
Features

- 100V/190A,
R_{DS (ON)} = 5mΩ (Typ.) @ V_{GS} = 10V
- Ultra Low On-Resistance
- Exceptional dv/dt capability
- Fast Switching and Fully Avalanche Rated
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free and Green Available

Applications

- Switching Application Systems

Pin Description



Absolute Maximum Ratings

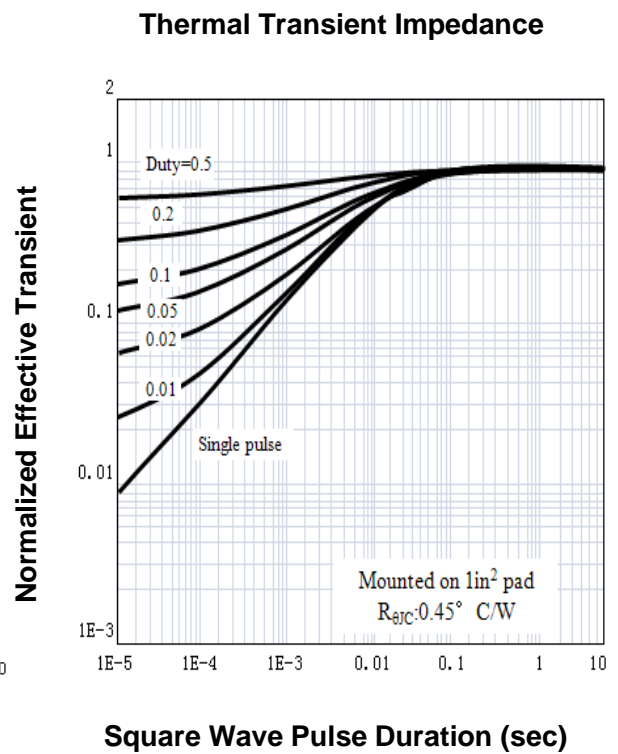
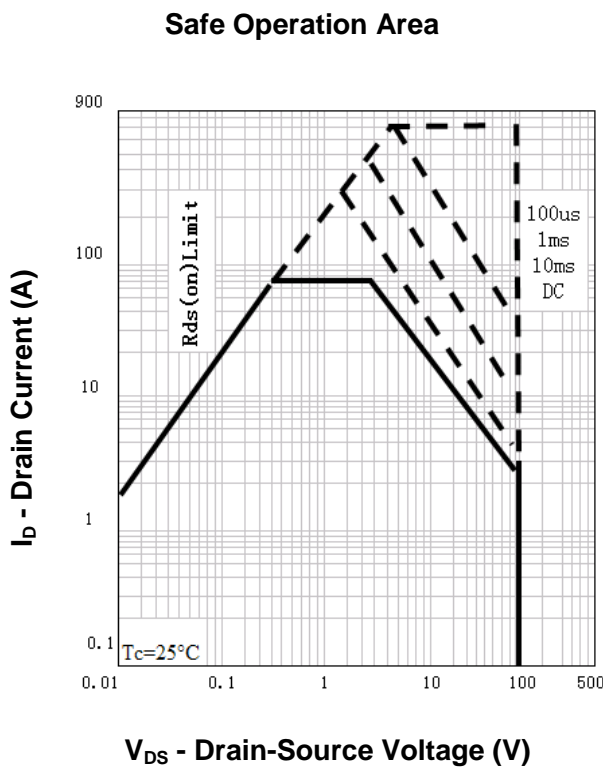
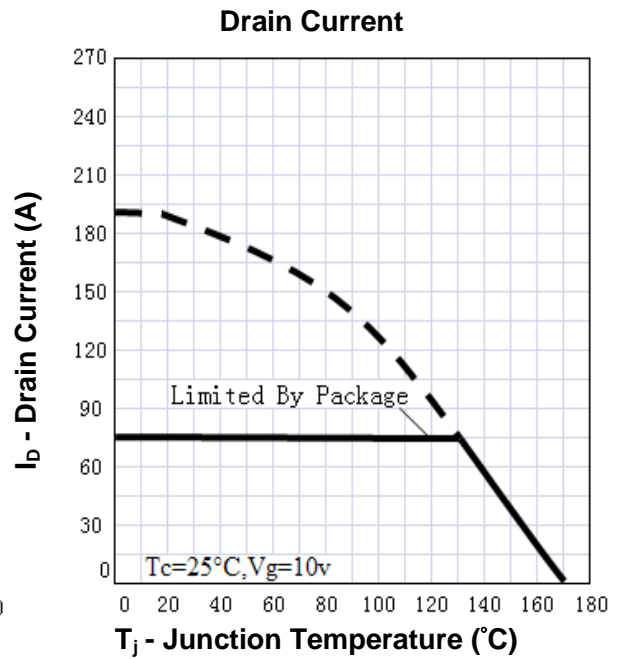
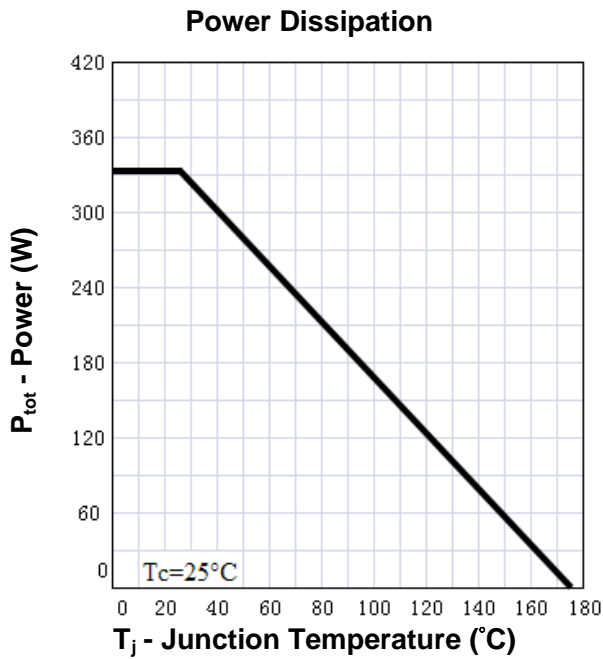
Symbol	Parameter	Rating	Unit
Common Ratings (T _A = 25°C Unless Otherwise Noted)			
V _{DSS}	Drain-Source Voltage	100	V
V _{GSS}	Gate-Source Voltage	±25	
T _J	Maximum Junction Temperature	175	°C
T _{STG}	Storage Temperature Range	-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C = 25°C 190 ^①	A
Mounted on Large Heat Sink			
I _{DP}	300µs Pulse Drain Current Tested	T _C = 25°C 720 ^②	A
I _D	Continuous Drain Current (V _{GS} = 10V)	T _C = 25°C 190 ^①	A
		T _C = 100°C 120 ^①	
P _D	Maximum Power Dissipation	T _C = 25°C 333	W
		T _C = 100°C 167	
R _{θJC}	Thermal Resistance-Junction to Case	0.45	°C/W
Drain-Source Avalanche Ratings			
E _{AS} ^③	Avalanche Energy, Single Pulsed	1240	mJ

Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU1H190R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1 30	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}$ ^④	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=80A$		5	6.5	m Ω
Diode Characteristics						
V_{SD} ^④	Diode Forward Voltage	$I_{SD}=80A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=80A, di_{SD}/dt=100A/\mu s$		89		ns
Q_{rr}	Reverse Recovery Charge			175		nC
Dynamic Characteristics ^⑤						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.2		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		6500		pF
C_{oss}	Output Capacitance			940		
C_{riss}	Reverse Transfer Capacitance			650		
$t_{d(ON)}$	Turn-on Delay Time			29		
t_r	Turn-on Rise Time	$V_{DD}=30V, R_L=30\Omega,$ $I_{DS}=80A, V_{GEN}=10V,$ $R_G=6\Omega$		38		
$t_{d(OFF)}$	Turn-off Delay Time			80		
t_f	Turn-off Fall Time			125		
Gate Charge Characteristics ^⑤						
Q_g	Total Gate Charge	$V_{DS}=80V, V_{GS}=10V,$ $I_{DS}=80A$		158		nC
Q_{gs}	Gate-Source Charge			35		
Q_{gd}	Gate-Drain Charge			52		

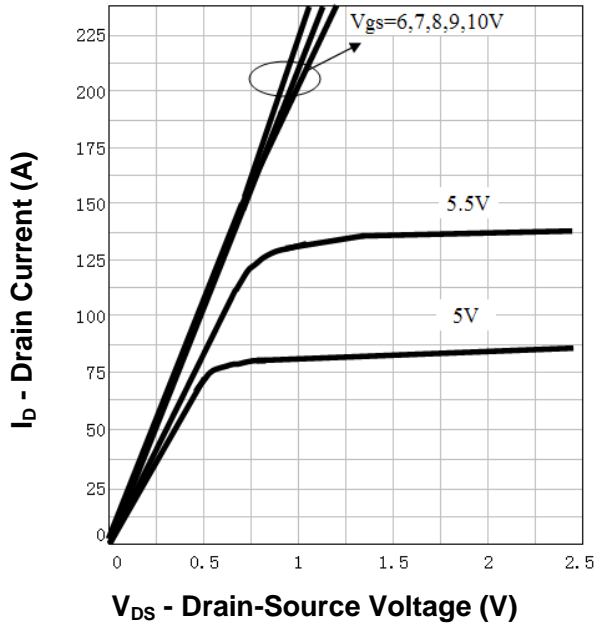
- Notes: ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
 ② Pulse width limited by safe operating area.
 ③ Limited by $T_{Jmax}, I_{AS}=65A, V_{DD}=48V, R_G=47\Omega$, Starting $T_J=25^\circ\text{C}$.
 ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

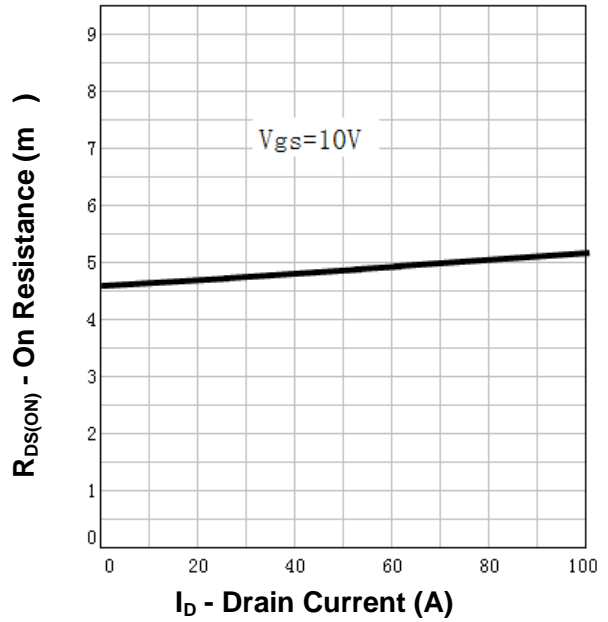


Typical Characteristics

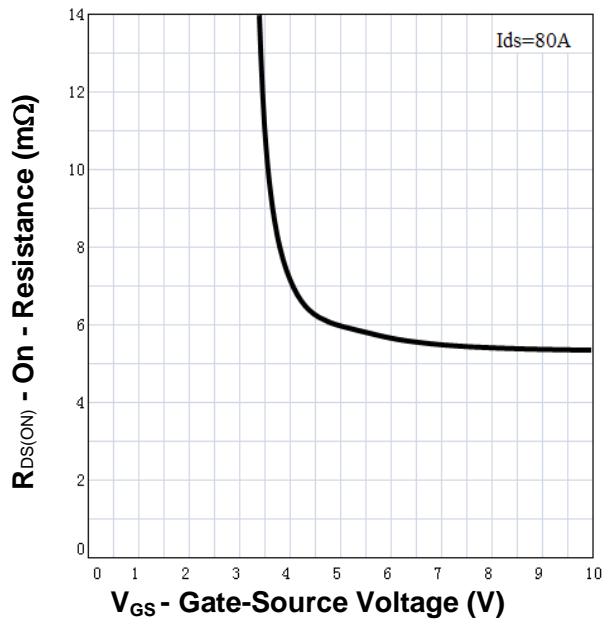
Output Characteristics



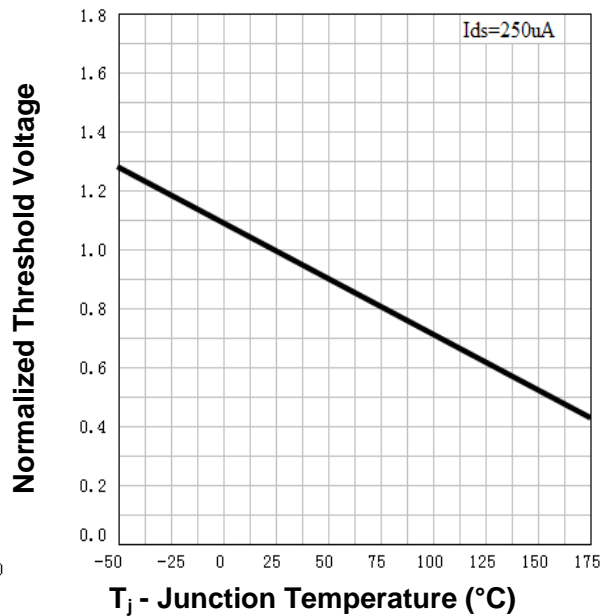
Drain-Source On Resistance



Drain-Source On Resistance

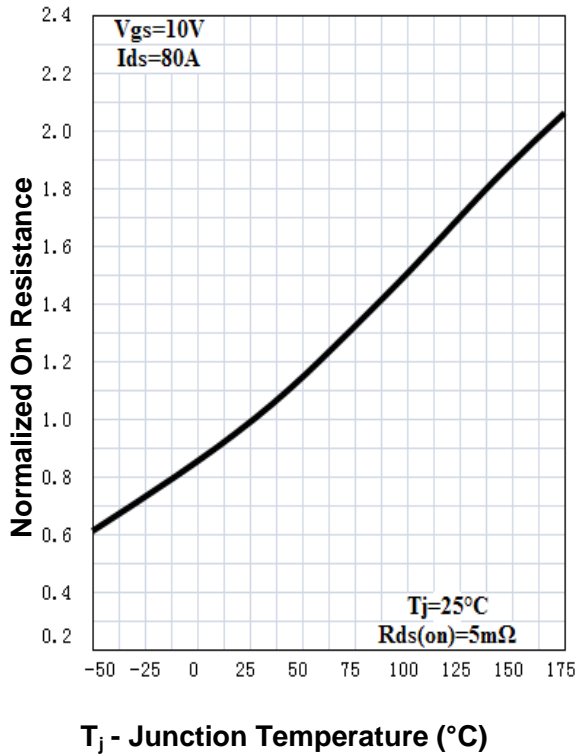


Gate Threshold Voltage

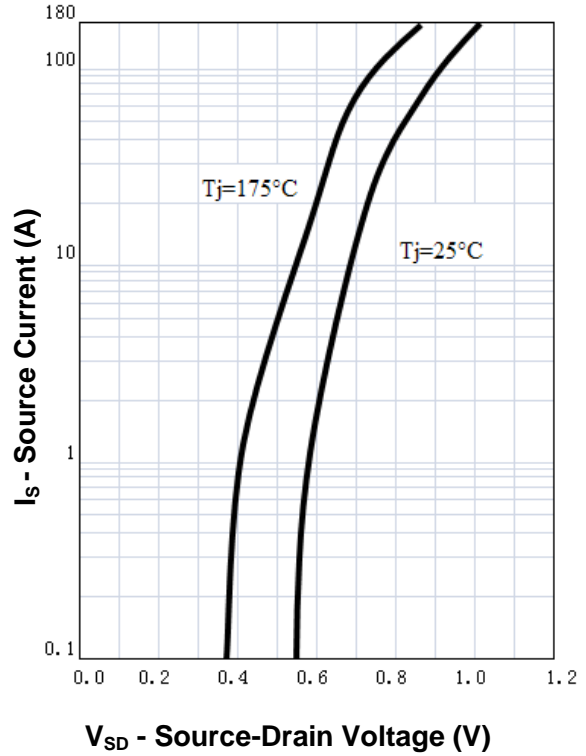


Typical Characteristics

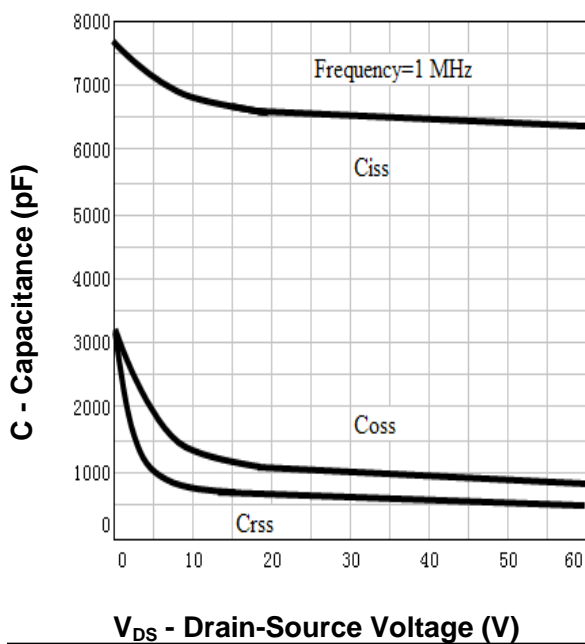
Drain-Source On Resistance



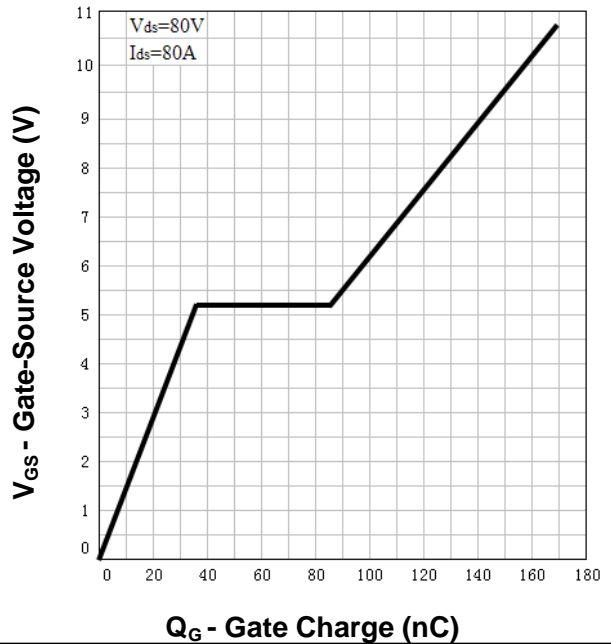
Source-Drain Diode Forward



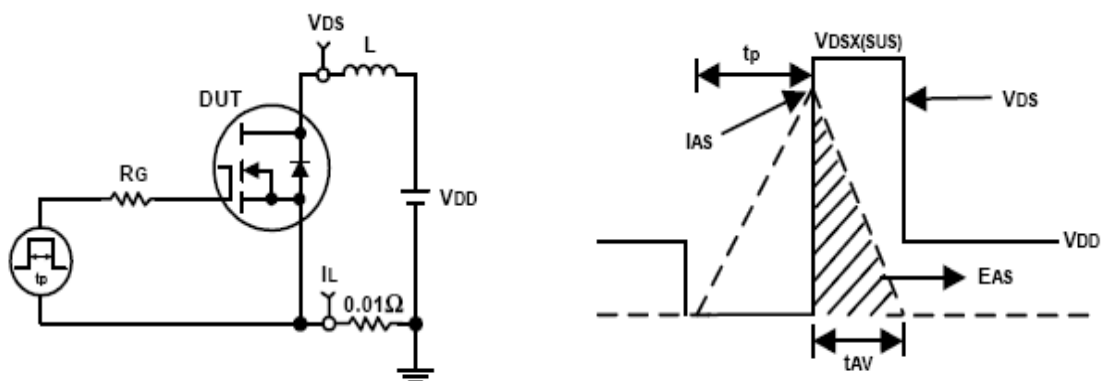
Capacitance



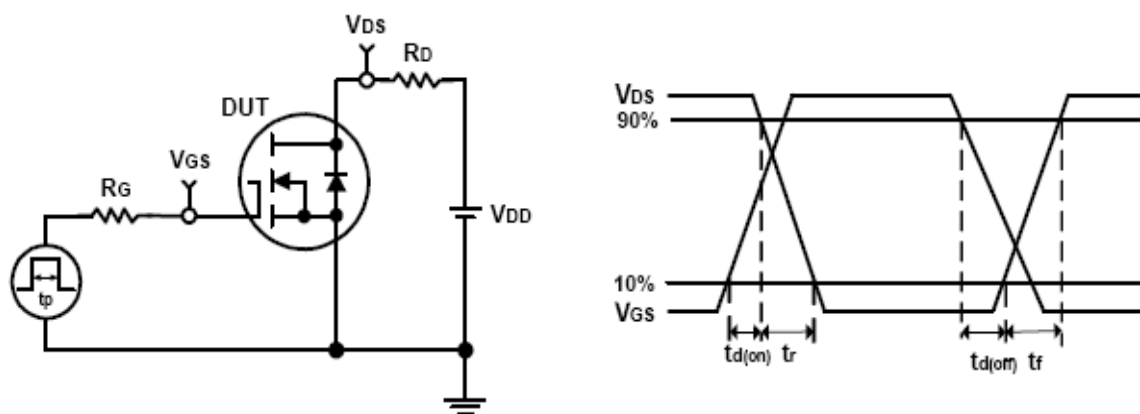
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

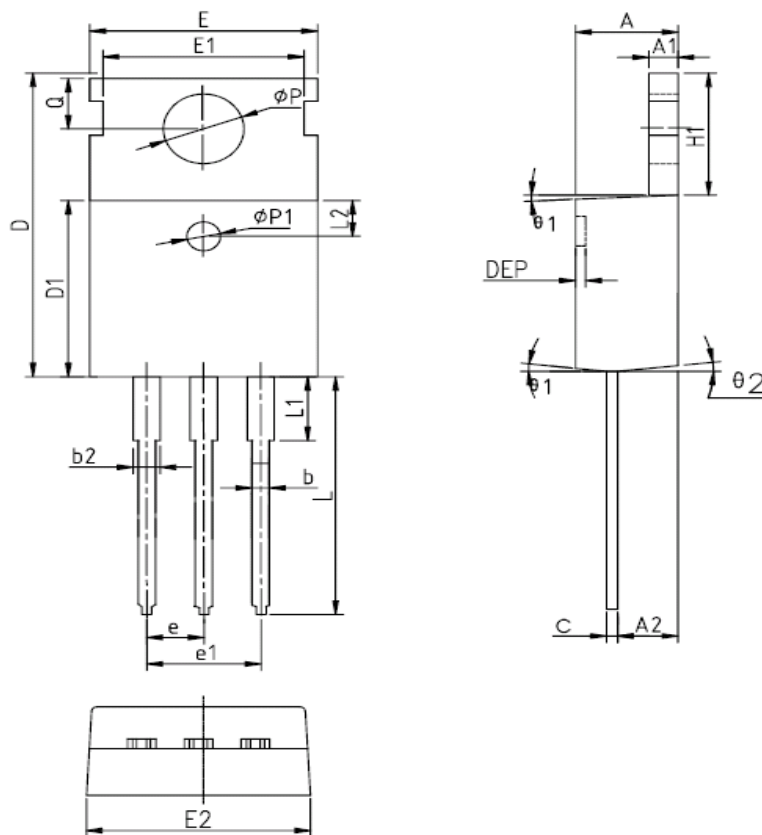


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU1H190R	RU1H190R	TO-220	Tube	50	-	-

Package Information

TO-220FB-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063
A1	1.27	1.30	1.33	0.050	0.051	0.052	e	2.54BSC			0.1BSC		
A2	2.35	2.40	2.50	0.093	0.094	0.098	e1	5.08BSC			0.2BSC		
b	0.77	-	0.90	0.030	-	0.035	H1	6.40	6.50	6.60	0.252	0.256	0.260
b2	1.23	-	1.36	0.048	-	0.054	L	12.75	-	13.17	0.502	-	0.519
C	0.48	0.50	0.52	0.019	0.020	0.021	L1	-	-	3.95	-	-	0.156
D	15.40	15.60	15.80	0.606	0.614	0.622	L2	2.50REF.			0.098REF.		
D1	9.00	9.10	9.20	0.354	0.358	0.362	ϕp	3.57	3.60	3.63	0.141	0.142	0.143
DEP	0.05	0.10	0.20	0.002	0.004	0.008	Q	2.73	2.80	2.87	0.107	0.110	0.113
E	9.70	9.90	10.10	0.382	0.389	0.398	$\theta 1$	5°	7°	9°	5°	7°	9°
E1	-	8.70	-	-	0.343	-	$\theta 2$	1°	3°	5°	1°	3°	5°
E2	9.80	10.00	10.20	0.386	0.394	0.401							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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